TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

# **2SJ200**

### **High Power Amplifier Application**

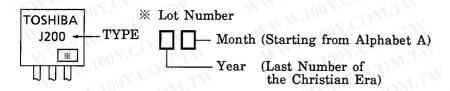
 $\begin{array}{ll} \bullet & \mbox{High breakdown voltage} & : V_{DSS} = -180 \ V \\ \bullet & \mbox{High forward transfer admittance} & : |Y_{fs}| = 4.0 \ S \ (typ.) \end{array}$ 

• Complementary to 2SK1529

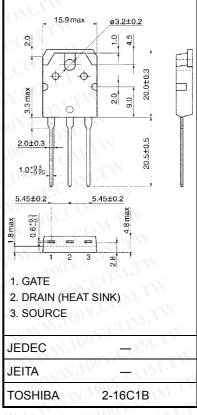
## Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DSS</sub>	-180	V
Gate-source voltage	V <sub>GSS</sub>	±20	V
Drain current (Note 1)	l <sub>D</sub>	-10	Α
Drain power dissipation (Tc = 25°C)	PD	120	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

#### Marking



#### Unit: mm



Weight: 4.6 g (typ.)

### Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = -180 V, V <sub>GS</sub> = 0	d -	-W	-1.0	mA
Gate leakage current	I <sub>GSS</sub>	V <sub>DS</sub> = 0, V <sub>GS</sub> = ±20 V			±0.5	μΑ
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0	-180	_	N W	V
Gate-source cut-off voltage (Note 2)	V <sub>GS</sub> (OFF)	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.1 A	-0.8	_	-2.8	N-V
Drain-source saturation voltage	V <sub>DS</sub> (ON)	I <sub>D</sub> = -6 A, V <sub>GS</sub> = -10 V		-1.5	-5.0	٧
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -3 \text{ A}$	DM-	4.0		S
Input capacitance	C <sub>iss</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	ONT.	1300	_	WW
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0, f = 1 MHz	COM.	350	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0, f = 1 MHz	LATON.	200	_	N V

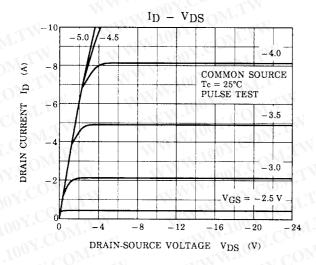
Note 1: Please use devices on condition that the channel temperature is below 150°C.

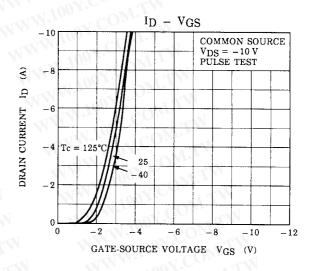
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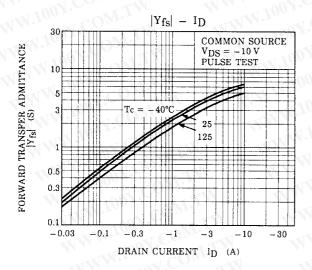
Note 2: V<sub>GS (OFF)</sub> Classification O: -0.8~-1.6, Y: -1.4~-2.8

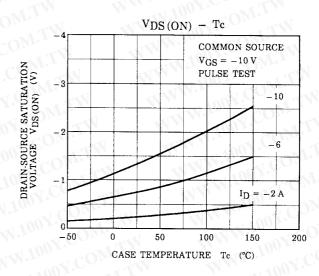
This transistor is an electrostatic sensitive device. Please handle with caution.

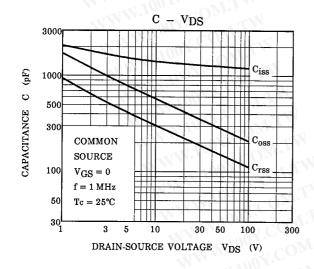
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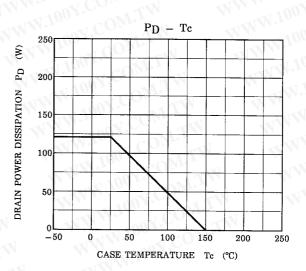




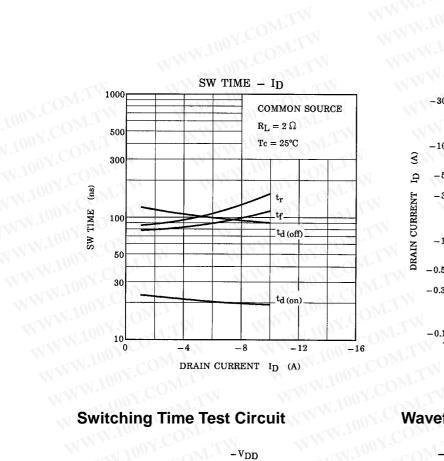


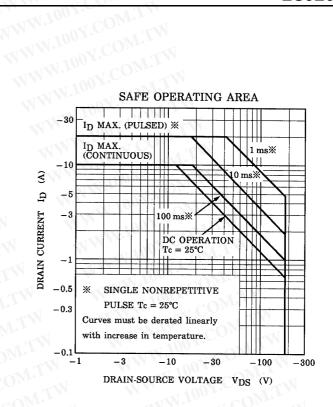


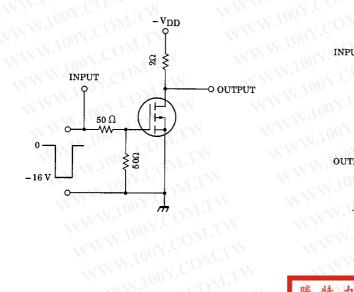




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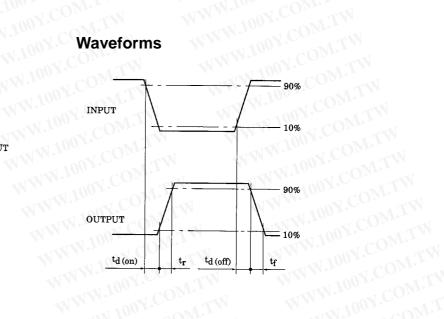






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#### **Waveforms**



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